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and formed on and adhering to a top of said first insulation layer; and

a third insulation layer comprising an inorganic material and formed on and adhering to a top of said second insulation layer.

2. (Amended) The semiconductor device according to claim 1, wherein said first insulation layer comprises at least one of an organopolysiloxane and an aromatic-containing organic resin.

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cont.
3. (Amended) The semiconductor device according to claim 1, wherein said second insulation layer comprises at least one of hydrogen silsesquioxane and a hydride organosiloxane.

4. (Amended) The semiconductor device according to claim 1, wherein said third insulation layer comprises at least one material selected from the group consisting of silicon oxide, silicon nitride and silicon oxynitride.

5. (Amended) A semiconductor wafer comprising:

a multi-layered insulation film formed on a surface of the wafer, said multi-layered insulation film comprising:

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a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon oxide dielectric constant;

a second insulation layer comprising a polysiloxane compound having an Si-H group and formed on and adhering to a top of said first insulation layer; and

a third insulation layer comprising an inorganic material and formed on and adhering

C² Conf to a top of said ~~second~~ insulation layer.

B¹ 6. (Amended) The semiconductor wafer according to claim 5, wherein said first insulation layer comprises at least one of an organopolysiloxane and an aromatic-containing organic resin.

7. (Amended) The semiconductor wafer according to claim 5, wherein said second insulation layer comprises at least one of hydrogen silsesquioxane and a hydride organosiloxane.

8. (Amended) The semiconductor wafer according to claim 5, wherein said third insulation layer is comprises at least one material selected from the group consisting of silicon oxide, silicon nitride and silicon oxynitride.

Please add the following new claims:


B² - - 31. (New) The semiconductor device according to claim 1, wherein said dielectric constant of said first insulation layer is no greater than 3.5.

32. (New) The semiconductor device according to claim 2, wherein said organopolysiloxane comprises at least one of an alkyl silsesquioxane and a hydride alkyl siloxane.

33. (New) The semiconductor device according to claim 2, wherein said aromatic-containing organic resin comprises at least one of a polyaryl ether and a divinyl siloxane-bis-benzocyclobutene.

34. (New) The semiconductor device according to claim 1, wherein said first insulation layer has a thickness greater than a thickness of said second insulation layer, and wherein said first insulation layer has a thickness greater than a thickness of said third insulation layer.

35. (New) The semiconductor device according to claim 1, wherein said second insulation layer comprises a first layer and a second layer placed in said first layer.


 36. (New) The semiconductor device according to claim 36, wherein said second layer comprises methyl silsesquioxane.

37. (New) The semiconductor device according to claim 1, further comprising:
a plurality of wires formed in said multi-layer insulation film.

38. (New) The semiconductor device according to claim 38, wherein said wires comprise copper wires.

39. (New) The semiconductor device according to claim 1, wherein said second insulation film comprises a methylated hydrogen silsesquioxane (MHSQ) film.

40. (New) The semiconductor device according to claim 39, wherein said MHSQ film has a thickness of about 50 nm.

 41. (New) A semiconductor device having a damascene wiring structure, said semiconductor

device comprising:

a multi-layered insulation film formed on a semiconductor substrate, said multi-layered insulation film having a plurality of recesses and comprising:

a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon oxide dielectric constant;

a second insulation layer comprising a polysiloxane compound having an Si-H group and formed on and adhering to a top of said first insulation layer; and

a third insulation layer comprising an inorganic material and formed on and adhering to a top of said second insulation layer; and

an electroconductive film formed in each recess of said plurality of recesses.

42. (New) A semiconductor device comprising a multi-layered insulation film formed on a semiconductor substrate said multi-layered insulation film comprising:

a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon dioxide dielectric constant;

a second insulation, adhesive layer comprising a polysiloxane compound having an Si-H group and formed on and being in contact with a top of said first insulation layer; and

a third insulation layer comprising an inorganic material and formed on and being in contact with a top of said second insulation, adhesive layer. - -

REMARKS

Applicant concurrently files herewith a Petition (and fee) for a One-Month Extension of Time.